RoHS
COMPLIANT

PNP General Purpose Amplifier

Features

- We declare that the material of product compliance : H ? W • ð @ P ` X ð d` O S O W @ 0 0D U

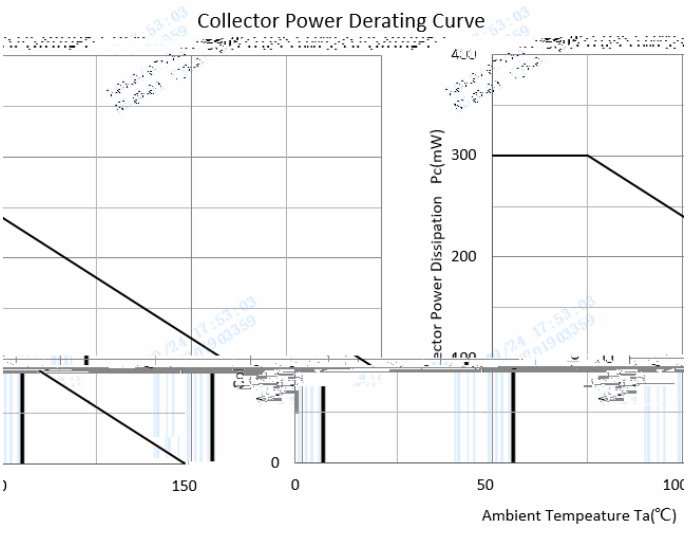
■ Maximum Ratings (Ta=25 Unless otherwise specified)

Item	Symbol	Unit	Conditions	Value
Collector-Base Voltage	V_{CBO}	V	IC=-100μA,IE=0	-80
Collector-Emitter Voltage	V_{CEO}	V	IC =-10mA,IB=0	-60
Emitter-Base Voltage	V_{EBO}	V	IE=-100μA,IC=0	-5
Collector Current	I_C	A		-1
Collector Power Dissipation	P_C	mW		300
Thermal Resistance From Junction to Ambient	$R_{\theta JA}$	/W		417
Operation Junction Temperature	T_J			150
Storage Temperature	T_{STG}			-55 to +150

■ Electrical Characteristics Ta=25 Unless otherwise specified

Item	Symbol	Unit	Conditions	Min	Type	Max
Collector-base breakdown voltage	$V_{(BR)CBO}$	V	IC=-100μA,IE=0	-80		
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	V	IC =-10mA,IB=0	-60		
Emitter-base breakdown voltage	$V_{(BR)EBO}$	V	IE=-100μA,IC=0	-5		
Collector-Base cut-off current	I_{CBO}	uA	V_{CB}=-60 V ,IE=0			-0.1
Emitter-Base cut-off current	I_{EBO}	uA	V_{EB}=-4V , IC=0			-0.1
DC current gain	$h_{FE}1$		VCE=-5V,IC=-1mA	100		
	$h_{FE}2$		VCE=-5V,IC=-500mA	100		300
	$h_{FE}3$		VCE=-5V,IC=-1A	80		
	$h_{FE}4$		VCE=-5V,IC=-2A	15		
Collector-emitter saturation voltage	$V_{CE(sat)}$	V	IC=-500mA,IB=-50mA			-0.3
		V	IC=-1A,IB=-100mA			-0.6
Base-emitter saturation voltage	$V_{BE(sat)}$	V	IC=-1A,IB=-100mA			-1.2
Base-emitter voltage	V_{BE}	V	VCE=-5V,IC=-1A			-1
Transition frequency	f_T	MHz	VCE=-10V, IC=-50mA,f=100MHz	150		
Collector-Base Output Capacitance	Cob	pF	V_{CB}=-10V ,IE=0, f=1MHz		10	

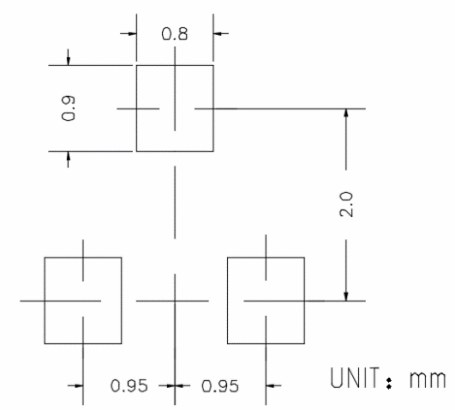
v(OHFWULFDO &KDUDFWHULVWLFV



■ **Ordering Information** (Example)

PREFERED P/N

■SOT-23 Soldering Footprint



SUGGESTED SOLDER PAD LAYOUT